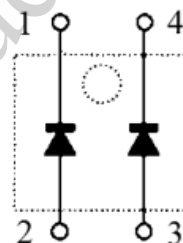
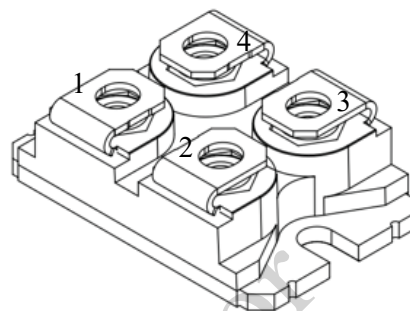


SiC SBD I3D12100SM

1200V SiC Schottky Diode

Features

- Ultra-Fast Switching
- Zero Reverse Recovery Current
- High-Frequency Operation
- Positive Temperature Coefficient on V_F
- High Surge Current
- 100% UIS tested



Benefits

- Improve System Efficiency
- Reduction of Heat Sink Requirement
- Essentially No Switching Losses
- Parallel Devices Without Thermal Runaway



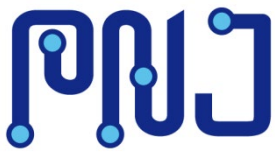
Application

- Consumer SMPS
- Boost Diodes in PFC or DC/DC Stages
- AC/DC Converters



Order Information

Part Number	Package	Marking
I3D12100SM	SOT-227	I3D12100SM



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PNJunction Semiconductor

1. Maximum Ratings

At $T_J = 25^\circ\text{C}$, unless specified otherwise (per Diode)

Parameter	Symbol	Value	Unit	Test condition
Repetitive Peak Reverse Voltage	V_{RRM}	1200	V	$T_C = 25^\circ\text{C}$
Surge Peak Reverse Voltage	V_{RSM}	1200	V	$T_C = 25^\circ\text{C}$
DC Blocking Voltage	V_R	1200	V	$T_C = 25^\circ\text{C}$
Forward Current	I_F	150 120 100	A	$T_C = 25^\circ\text{C}$ $T_C = 65^\circ\text{C}$ $T_C = 85^\circ\text{C}$
Repetitive Peak Forward Surge Current	I_{FRM}	300	A	$T_C = 25^\circ\text{C}$, $t_p = 10\text{ms}$
Non-Repetitive Forward Surge Current	I_{FSM}	390	A	$T_C = 25^\circ\text{C}$, $t_p = 10\text{ms}$
Power Dissipation	P_{tot}	450	W	$T_C = 25^\circ\text{C}$
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to +175	$^\circ\text{C}$	

2. Thermal Characteristics

Parameter	Symbol	Values	Unit
Thermal Resistance from Junction to Case	$R_{\theta JC}$	0.32	$^\circ\text{C}/\text{W}$

3. Electrical Characteristics

At $T_J = 25^\circ\text{C}$, unless specified otherwise (per Diode)

Parameter	Symbol	Values			Unit	Test condition
		Min.	Typ.	Max.		
Forward Voltage	V_F	/	1.6	1.7	V	$I_F = 100\text{A}$, $T_J = 25^\circ\text{C}$
			2.5	/		$I_F = 100\text{A}$, $T_J = 175^\circ\text{C}$
Reverse Current	I_R	/	10	100	μA	$V_R = 1200\text{V}$, $T_J = 25^\circ\text{C}$
			100	/		$V_R = 1200\text{V}$, $T_J = 175^\circ\text{C}$
Total Capacitance	C	/	4670	/	pF	$V_R = 1\text{V}$, $T_J = 25^\circ\text{C}$ $f = 1\text{MHz}$
			400			$V_R = 400\text{V}$, $T_J = 25^\circ\text{C}$ $f = 1\text{MHz}$
			339			$V_R = 800\text{V}$, $T_J = 25^\circ\text{C}$ $f = 1\text{MHz}$
Total Capacitive Charge	Q_C	/	454	/	nC	$V_R = 800\text{V}$
Capacitance Stored Energy	E_C	/	110	/	μJ	$V_R = 800\text{V}$

4. Typical Performance

At $T_J = 25^\circ\text{C}$, unless specified otherwise

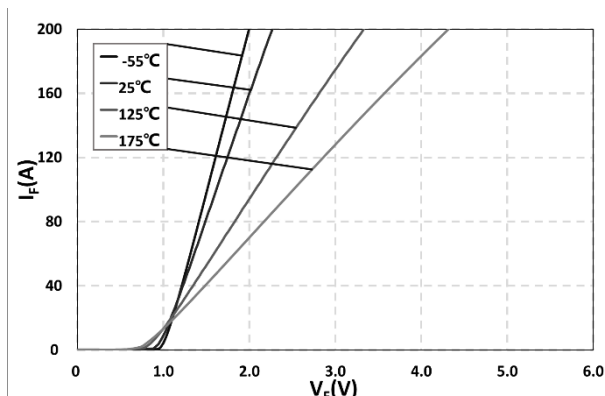


Fig. 1 Typical Forward Characteristics
 $I_F = f(V_F)$; $T_J = -55^\circ\text{C}, 25^\circ\text{C}, 125^\circ\text{C}, 175^\circ\text{C}$

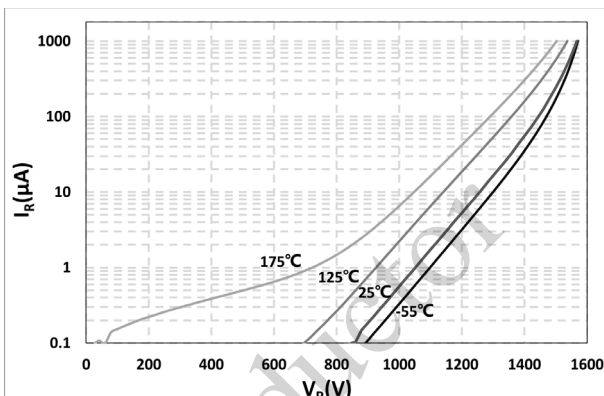


Fig. 2 Reverse Characteristics
 $I_R = f(V_R)$; $T_J = -55^\circ\text{C}, 25^\circ\text{C}, 125^\circ\text{C}, 175^\circ\text{C}$

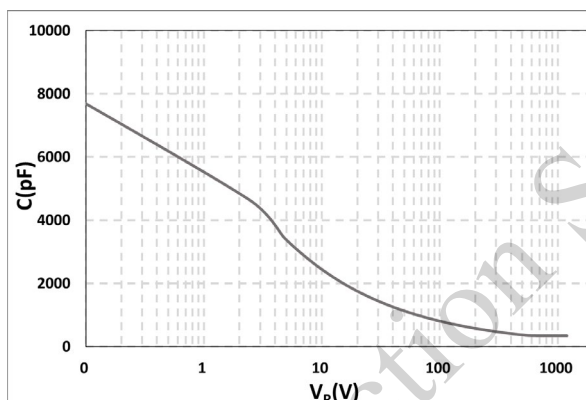


Fig. 3 Typical Total Capacitance
 $C = f(V_R)$

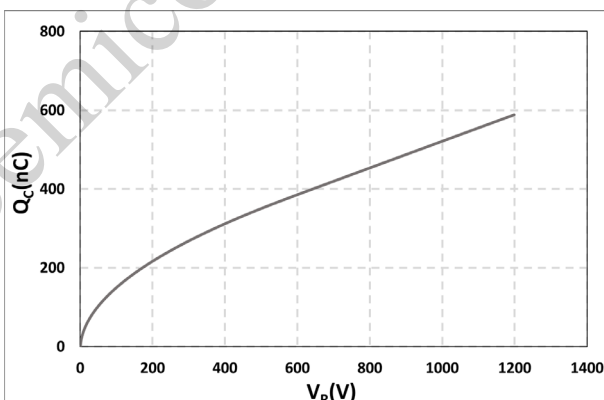


Fig. 4 Typical Total Capacitive Charge
 $Q_C = f(V_R)$

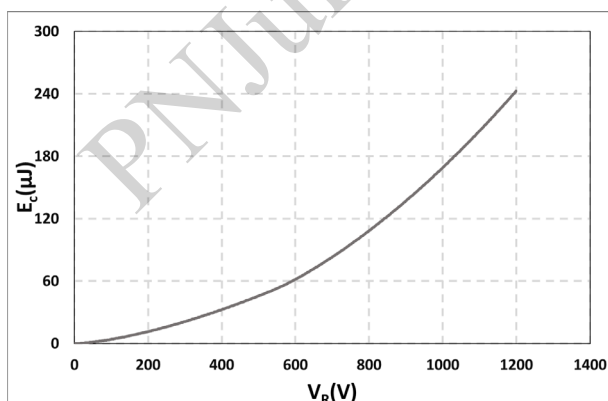


Fig. 5 Capacitance Stored Energy
 $E_C = f(V_R)$

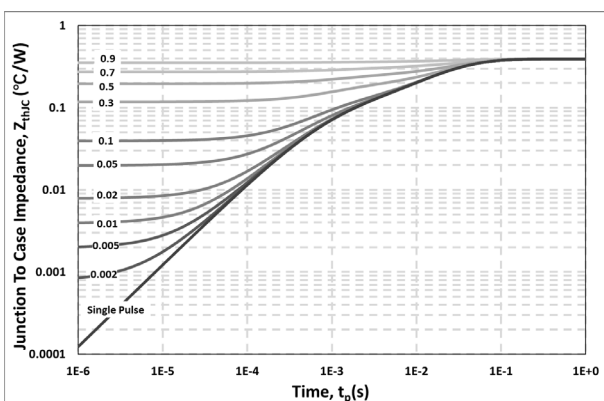


Fig. 6 Transient Thermal Impedance

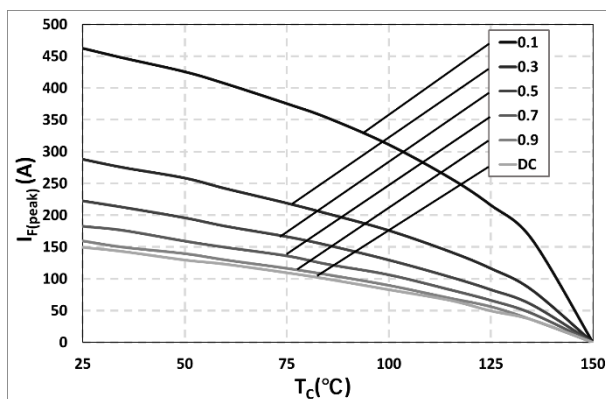


Fig. 7 Current Derating

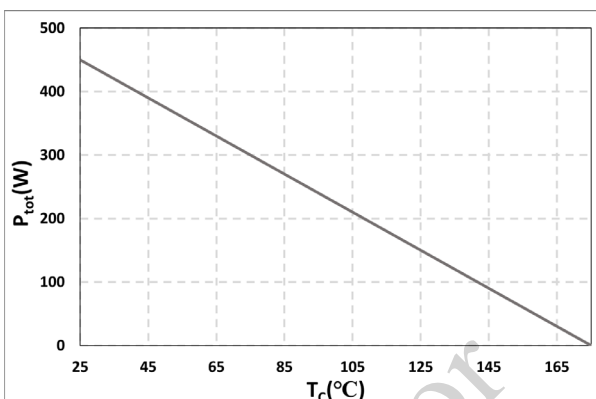
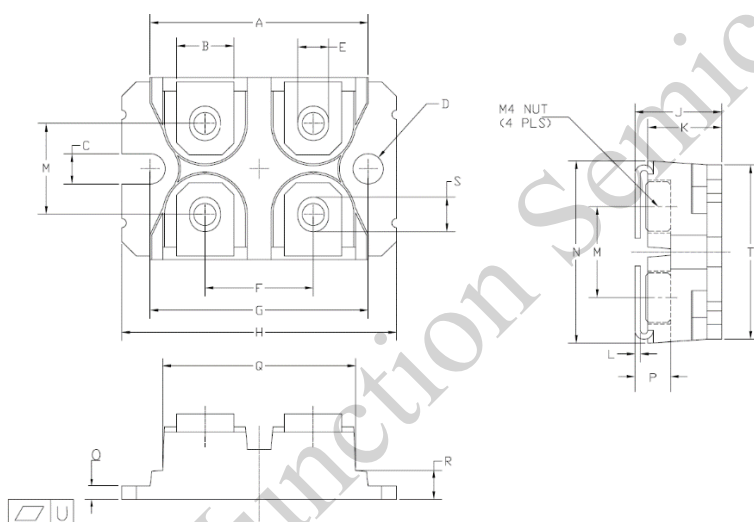


Fig. 8 Typical Power Derating
 $P_{tot} = f(T_c)$

5. Package Outlines



SYMBOL	MIN.	NOM.	MAX.
A	31.50	31.69	31.88
B	7.80	8.00	8.20
C	4.09	4.19	4.29
D	4.09	4.19	4.29
E	4.09	4.19	4.29
F	14.91	15.01	15.11
G	30.12	30.21	30.30
H	38.00	38.11	38.23
J	11.68	11.95	12.22
K	8.92	9.26	9.60
L	0.76	0.80	0.84
M	12.60	12.73	12.85
N	25.15	25.29	25.42
O	2.00	2.06	2.13
P	4.95	5.46	5.97
Q	26.54	26.72	26.90
R	3.94	4.18	4.42
S	4.72	4.79	4.85
T	24.59	24.83	25.07
U	-0.05	0.03	0.10

Drawing and Dimensions



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